

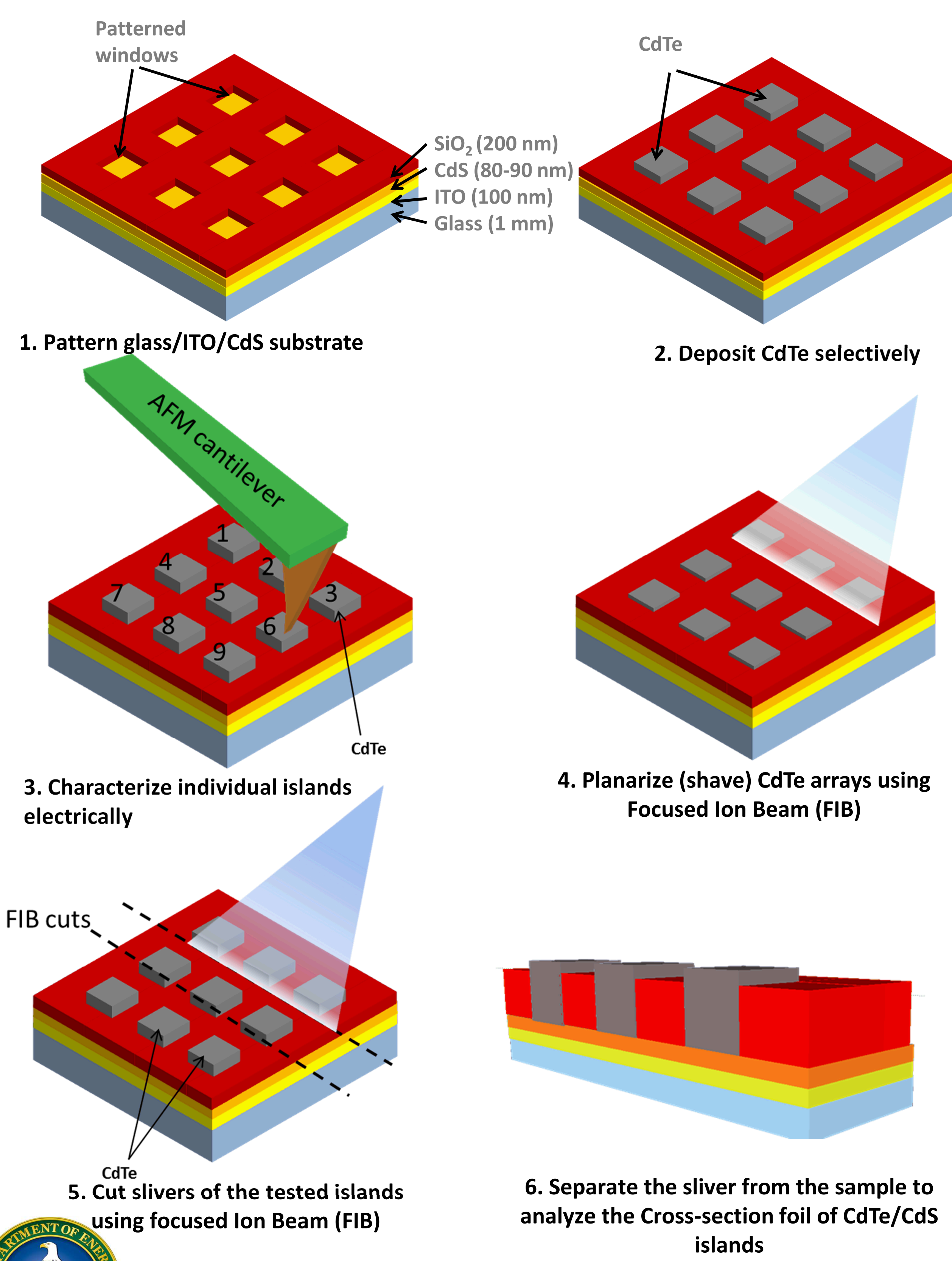
Motivation

Polycrystalline CdTe thin films are grown with defects that affect the electrical performance of solar cells. A characterization technique is needed to differentiate the beneficial from the detrimental effect. Open circuit voltages could be highly increased if detrimental defects are reduced.

Objective

- Develop a fabrication technique to isolate defects in CdTe solar cells.
- Develop a characterization method to make a one-to-one electrical-structural correlation in CdTe solar cells.

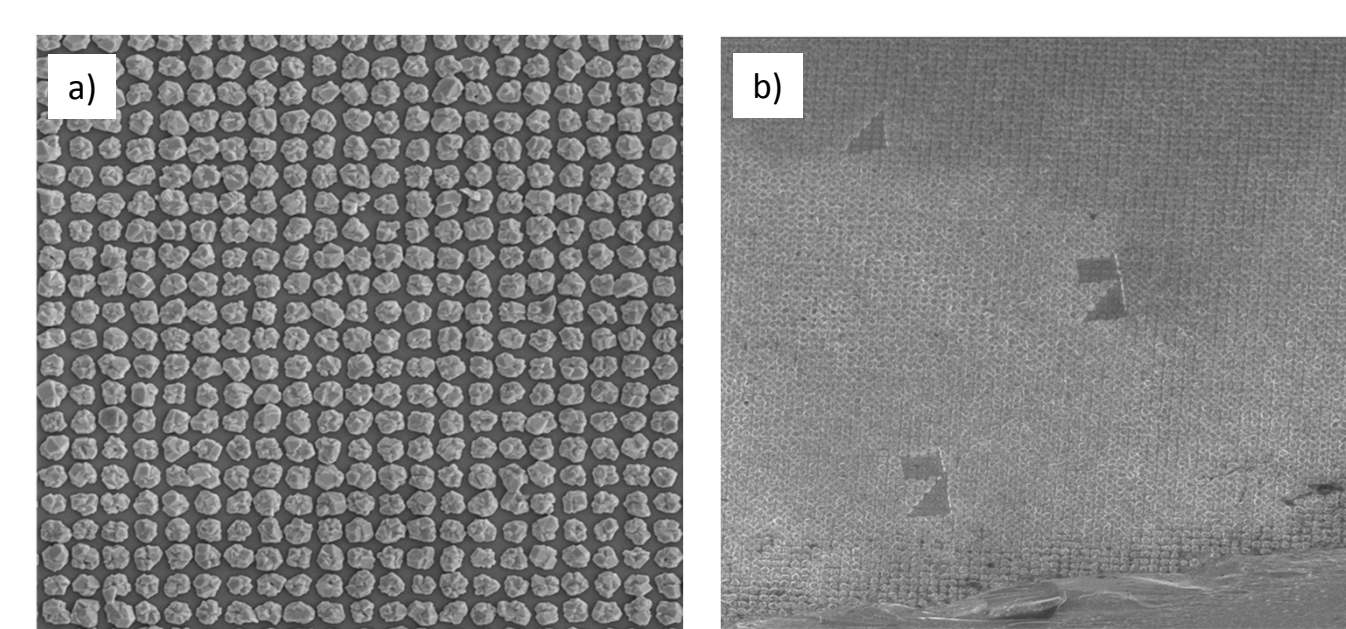
Method



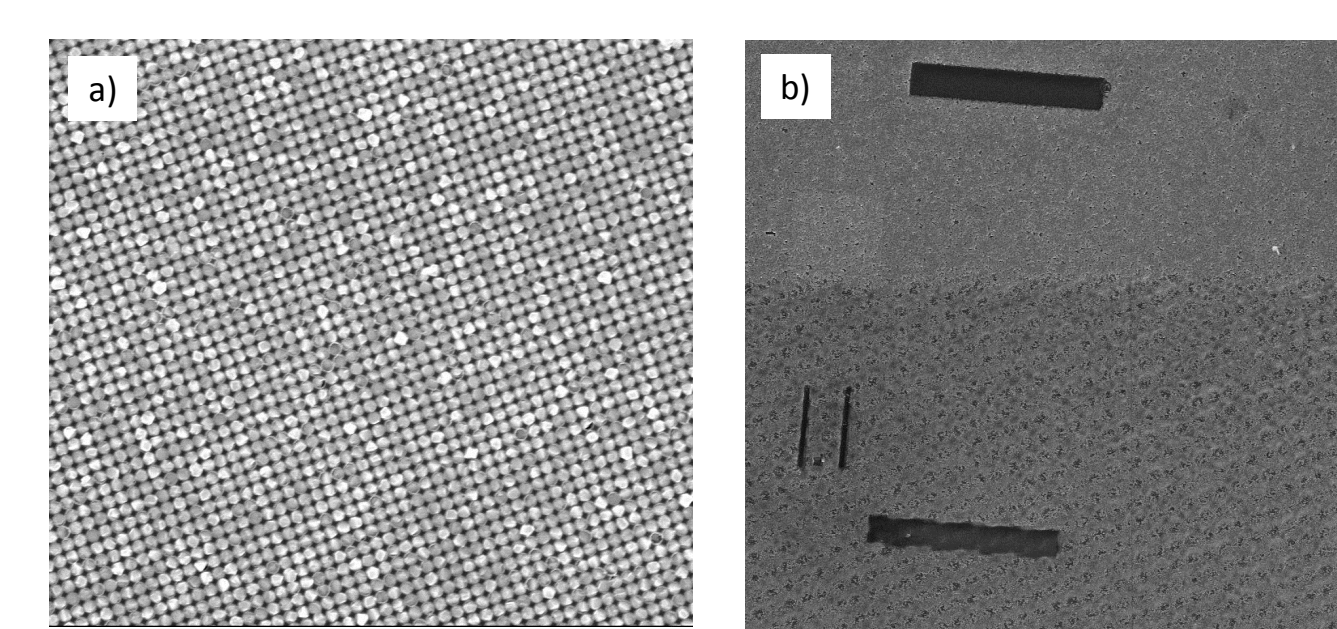
Fabrication

- 2 μm and 300 nm-feature size SiO₂ windows were fabricated on glass/ITO/CdS substrates.
- CdTe was deposited only inside each micro and nano SiO₂ window and nowhere else.
- Micro and nano-pn junctions were indexed, identified and prepared for EBSD and TEM

Micro-islands



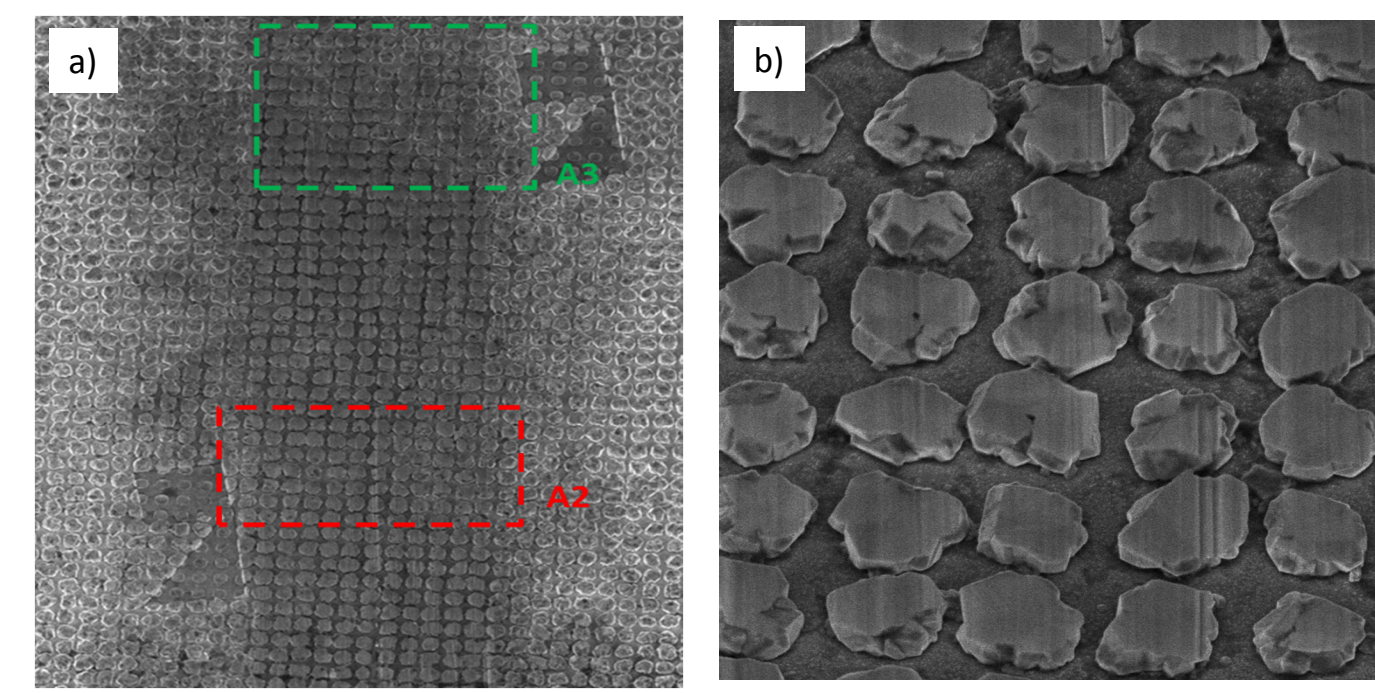
Nano-islands



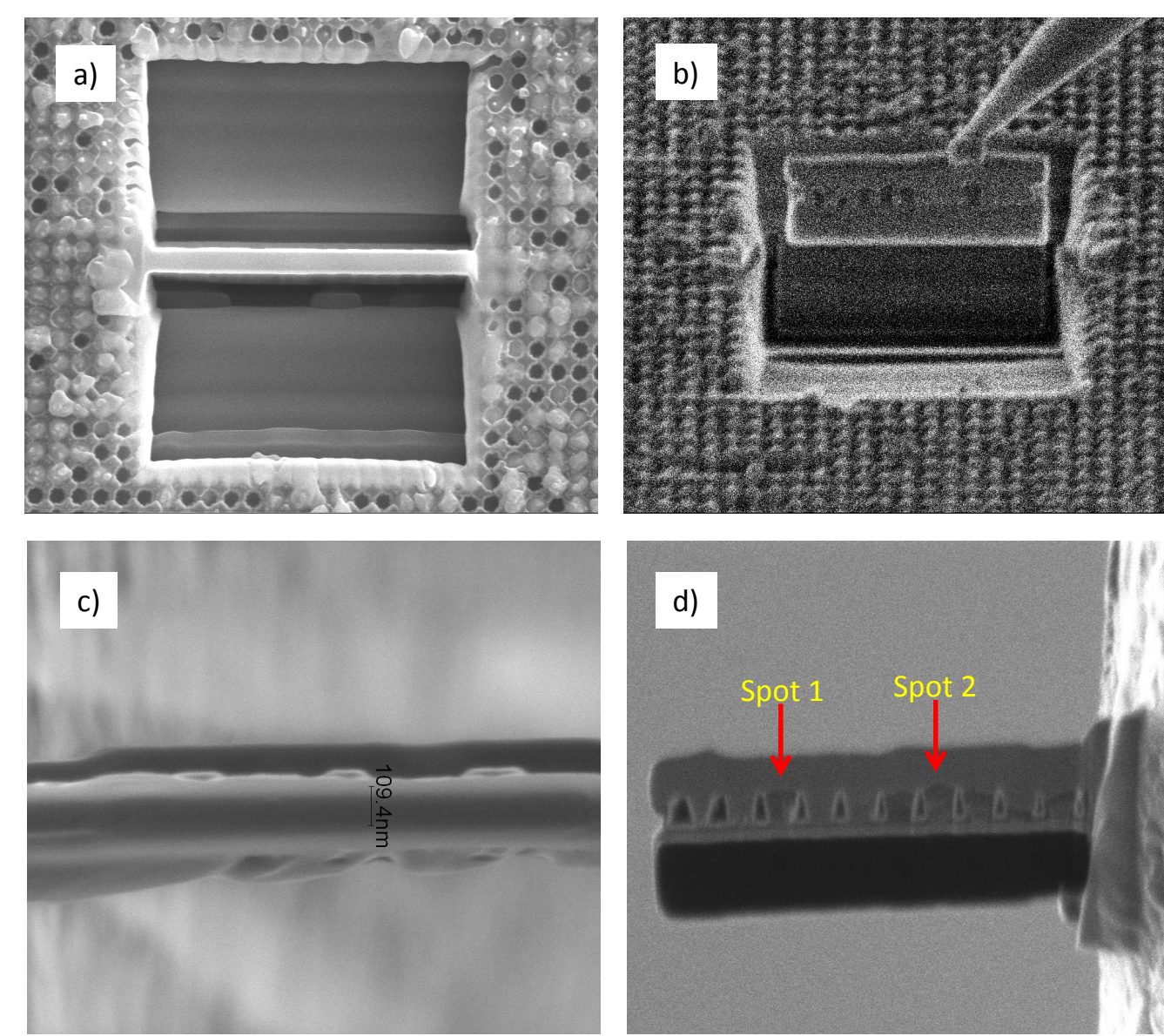
Sample Preparation

- Surface and cross-section of CdTe arrays were prepared for crystal orientation and defect studies
- The surface of CdTe micro-islands was shaved using a dual-beam SEM/FIB system for EBSD characterization
- Thin foils were prepared from CdTe nano-islands for TEM characterization.

Micro-islands



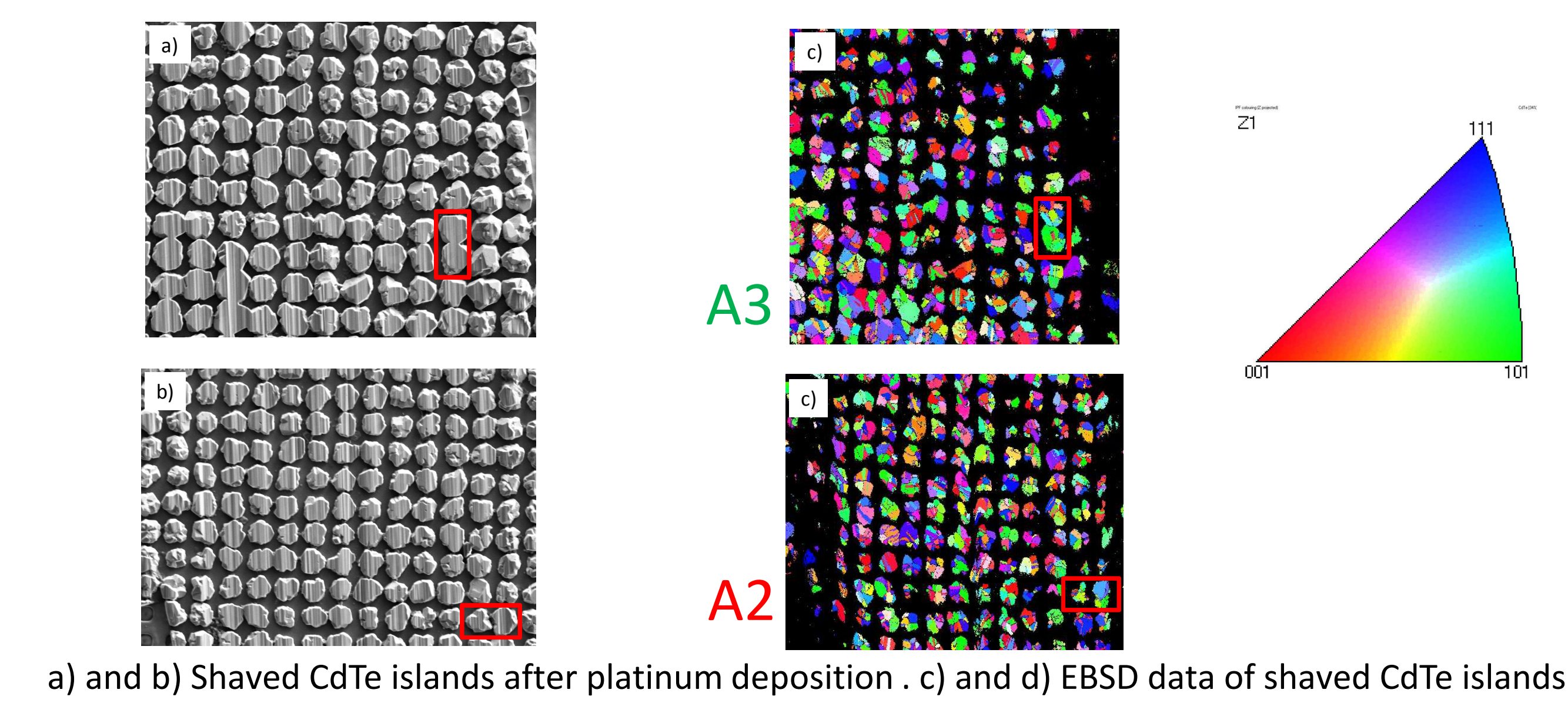
Nano-islands



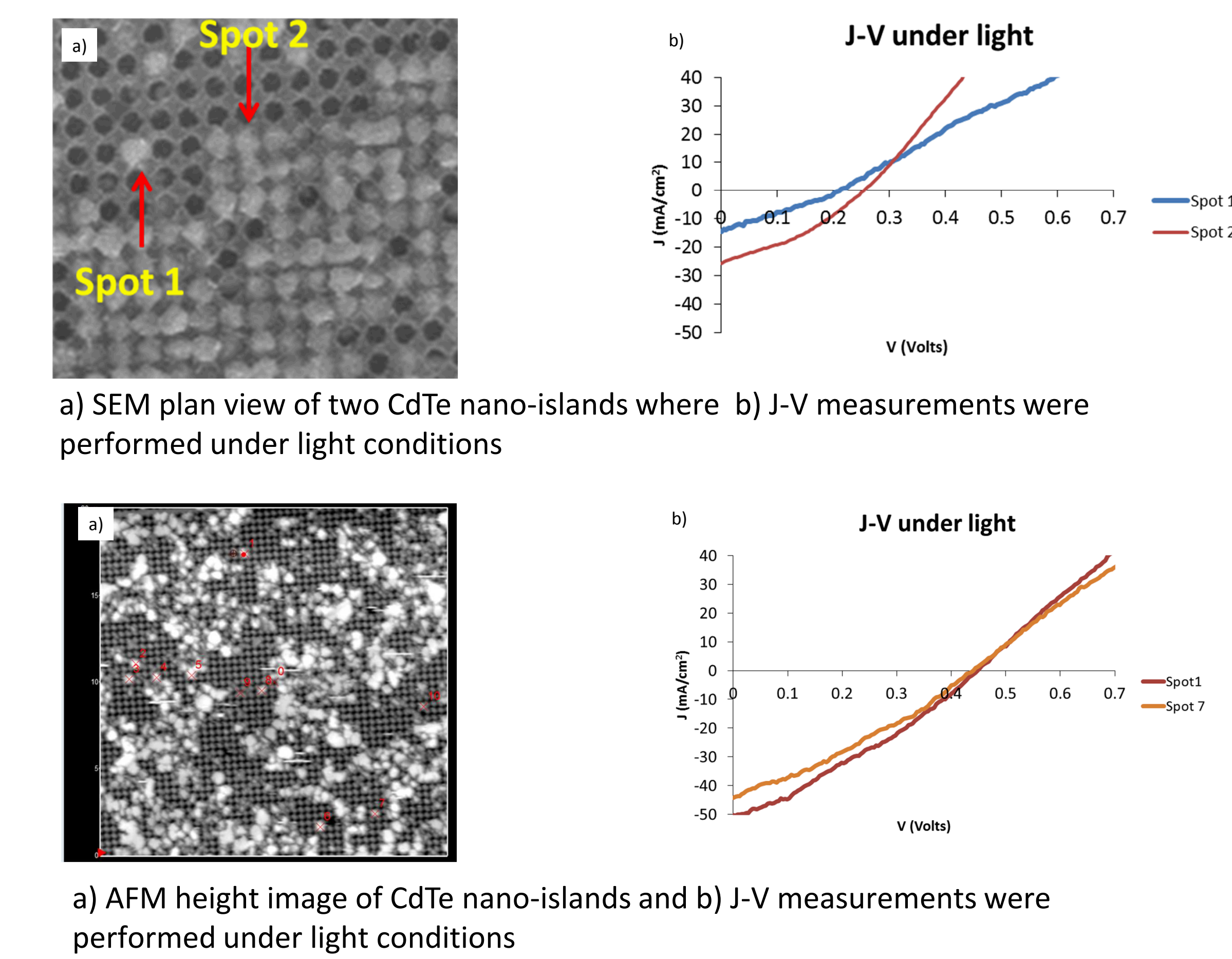
Results

- Number of grains per island were obtained from EBSD.
- Grain orientation per island is known.
- CdTe islands were successfully indexed and identified.
- Nano-pn junctions were successfully tested under light bias.
- Nano-pn junctions convert light into electricity.

Microstructure



Electrical



Conclusions

- Selective-area growth was used to isolate CdTe grains and test their atomic structure.
- EBSD was successfully performed and reveals crystallographic orientation.
- J-V measurements under light show operational nano-solar cells.